

MPS-A92 is PNP silicon planar epitaxial transistor designed for general purpose applications requiring high breakdown voltage, low saturation voltage and low capacitance.

TO-92A



EBC

ABSOLUTE MAXIMUM RATINGS

Collector-Emitter Voltage	V _{CEO}	300V
Collector-Base Voltage	V _{CBO}	300V
Emitter-Base Voltage	V _{EB0}	5V
Collector Current	I _C	500mA
Total Power Dissipation @ T _A =25°C T _C =25°C	P _{tot}	625mW 1.5W
Operating Junction & Storage Temperature	T _j , T _{stg}	-55 to +150°C

ELECTRICAL CHARACTERISTICS (T_A=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITIONS
Collector-Emitter Breakdown Voltage	BV _{CEO}	300		V	I _C =1mA I _B =0
Collector-Base Breakdown Voltage	BV _{CBO}	300		V	I _C =100μA I _E =0
Emitter-Base Breakdown Voltage	BV _{EB0}	5		V	I _E =10μA I _C =0
Collector Cutoff Current	I _{CBO}		250	nA	V _{CB} =200V, I _E =0
Emitter Cutoff Current	I _{EB0}		100	nA	V _{EB} '=3V I _C =0
D.C. Current Gain	H _{FE}	25 40 25			I _C =1mA V _{CE} =10V I _C =10mA V _{CE} =10V I _C =30mA V _{CE} =10V
Collector-Emitter Saturation Voltage	V _{CE(sat)}		0.5	V	I _C =20mA I _B =2mA
Base-Emitter Saturation Voltage	V _{BE(sat)}		0.9	V	I _C =20mA I _B =2mA
Current Gain Bandwidth Product	f _T	50		MHz	I _C =10mA V _{CE} =20V f=20MHz
Output Capacitance	C _{ob}		6	pF	V _{CB} =20V I _E =0 f=1MHz



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